

Form PTO-1449 (Rev. 8-83)		U.S. Department of Commerce Patent and Trademark Office		Atty Docket 0756-2326		Serial No. 09/879,090	
INFORMATION DISCLOSURE STATEMENT <div style="border: 1px solid black; border-radius: 50%; width: 100px; height: 100px; display: flex; align-items: center; justify-content: center; margin: 0 auto;"> <div style="writing-mode: vertical-rl; transform: rotate(180deg); font-size: 8px;">PATENT & TRADEMARK OFFICE</div> <div style="text-align: center;"> 015 JUL 31 2001 </div> </div>				Applicants: Satoshi YOSHIMOTO			
				Filing Date: June 13, 2001		Group Art Unit: Unassigned	
U.S. PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)	
<i>not considered</i> <div style="border-left: 2px solid black; height: 100px; margin-left: 5px;"></div>	5,247,190	09/21/1993	Friend et al.				
	5,264,072	11/23/1993	Mukai				
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	5,594,569	01/14/1997	Konuma et al.				
	5,643,826	07/01/1997	Ohtani et al.				
	5,817,548	10/06/1998	Noguchi et al.				
	5,893,730	04/13/1999	Yamazaki et al.				
	5,923,962	07/13/1999	Ohtani et al.				
FOREIGN PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No	
<i>not considered</i> <div style="border-left: 2px solid black; height: 100px; margin-left: 5px;"></div>	07-130652	05/19/1995	JP			Eng Abst	
	10-092576	04/10/1998	JP			Eng Abst	
	90/13148	11/01/1990	WO			Full Eng	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
Examiner Initial							
<i>not considered</i> <div style="border-left: 2px solid black; height: 100px; margin-left: 5px;"></div>	Ishihara et al., "Location-Controlled Adjacent Grains Following Excimer-Laser Melting of Si Thin-Films", pp. 153-156, 1998, AM-LCD, TFTP1-3						
	Ishihara et al., "Location Control of Large Grain Following Excimer-Laser Melting of Si Thin-Films", pp. 1071-1075, March 1998, Jpn J. Appl. Phys. Vol. 37, No. 3B						
	Mariucci et al., "Lateral Growth Control in Excimer Laser Crystallized Polysilicon", pp. 137-142, 1999, Thin Solid Films 337						
	Schenk et al., "Polymers for Light Emitting Diodes", pp. 33-37, September 6-9, 1999, Euro Display '99, The 19th International Display Research Conference						
	Shimizu et al., "High-Mobility Poly-Si Thin-Film Transistors Fabricated by a Novel Excimer Laser Crystallization Method", pp. 112-117, January 1993, IEEE Transactions on Electron Devices, Vol. 40, No. 1						
	Yoshimoto et al., "Excimer-Laser Produced and Two-Dimensionally Position-Controlled Giant Si Grains on Organic SOG Underlayer", pp. 285-286, July 12-14, 2000, Digest of Technical Papers, AM-LCD 2000, International Workshop on Active-Matrix Liquid-Crystal Displays						
	Specifications and Drawings for Application Serial No. 09/570,612, "Semiconductor Device and Method for its Fabrication", Filing Date: 05/12/2000, Inventors: Shunpei YAMAZAKI et al.						
	Specifications and Drawings for Application Serial No. 09/612,100, "Method for Manufacturing a Semiconductor Device", Filing Date: 07/07/2000, Inventors: Ritsuko KAWASAKI et al.						
Specifications and Drawings for Application Serial No. 09/640,077, "Semiconductor Device and Method of Fabricating the Same", Filing Date: 08/17/2000, Inventors: Ritsuko KAWASAKI et al.							
Examiner	Vikki Trih			Date Considered 8/31/04			

***EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

07/26/2001

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